

iscN-Channel MOSFET Transistor

SiHB22N60EL

• FEATURES

- Low drain-source on-resistance:
 R_{DS}(ON) =0.197Ω (MAX)
- Enhancement mode:
 Vth = 3.0 to 5.0V (Vps = 10 V, Ip=0.25mA)
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

DESCRITION

· Switching Voltage Regulators

pin 1.Gate 2.Drain 3.Source TO-263 package

• ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{DSS}	Drain-Source Voltage	600	V
V _G s	Gate-Source Voltage	±30	V
l _D	Drain Current-Continuous	21	Α
Ірм	Drain Current-Single Pulsed	45	Α
P_D	Total Dissipation @Tc=25°C	227	W
Tj	Max. Operating Junction Temperature	-55~150	${\mathbb C}$
T _{stg}	Storage Temperature	-55~150	$^{\circ}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT	
Rth(ch-c)	Channel-to-case thermal resistance	0.55	°C/W	

	A B	K		S
J	D —		Q R	U
F		m	m	v -
	DIM	MIN	MAX	1
	A	MIN	0	1
	B	6.6	6.8	1
	C	15.23	15.25	1
	Ď	10.15	10.17	1
	F	0.76	0.78	1
	G	1.26	1.28	1
	Н	1.4	1.6	
	J	1.33	1.35	
	K	0.4	0.6	
	L	4.6	4.8	
		0.00	8.71	
	Q	8.69		4
	R	5.28	5.30	1
	R	5.28 1.26	5.30 1.28	
	R S U	5.28 1.26 0.0	5.30 1.28 0.2	
	R	5.28 1.26	5.30 1.28	

isc website: www.iscsemi.cn

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ELECTRICAL CHARACTERISTICS

Tc=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	MAX	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D = 0.25mA	600			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = 10V; I _D =0.25mA	3.0		5.0	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =10V; I _D =11A			0.197	Ω
lgss	Gate-Source Leakage Current	V _{GS} = ±30V;V _{DS} = 0V			±1	uA
I _{DSS}	Drain-Source Leakage Current	V _{DS} =600V; V _{GS} = 0V V _{DS} =480V; V _{GS} = 0V;T _J =150°C			1 10	uA
V _{SDF}	Diode forward voltage	I _{DR} =11A, V _{GS} = 0 V			1.2	V

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